

30 V, 400 mA dual N-channel Trench MOSFET Rev. 1 — 1 August 2011

Product data sheet

Product profile 1.

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- ESD protection up to 2 kV
- AEC-Q101 qualified
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	30	V
V _{GS}	gate-source voltage		-8	-	8	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	<u>[1]</u> _	-	400	mA
Static cha	racteristics (per transiste	or)				
R _{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \ V; \ I_{D} = 350 \ mA; \\ T_{j} = 25 \ ^{\circ}C \end{array}$	-	1	1.4	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2.	Pinning	g information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		54 52
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2	0	$G1 \left(\begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$
5	G2	gate TR2		
6	D1	drain TR1	SOT666 (SOT666)	S1 S2 017aaa256

3. Ordering information

Table 3. Ord	lering information		
Type number	Package		
	Name	Description	Version
NX3008NBKV	SOT666	plastic surface-mounted package; 6 leads	SOT666

4. Marking

Table 4.	Marking	codes
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Type number	Marking code ^[1]
NX3008NBKV	AA

[1] % = placeholder for manufacturing site code.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{DS}	drain-source voltage	T _j = 25 °C	-	30	V
V _{GS}	gate-source voltage		-8	8	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	<u>[1]</u> _	400	mA
		$V_{GS} = 4.5 \text{ V}; \text{ T}_{amb} = 100 \text{ °C}$	<u>[1]</u> _	260	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$	-	1.6	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	330	mW
			<u>[1]</u> _	390	mW
		T _{sp} = 25 °C	-	1090	mW
Per device	•				
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2] _	500	mW
Tj	junction temperature		-55	150	°C
T _{amb}	ambient temperature		-55	150	°C
T _{stg}	storage temperature		-65	150	°C
Source-dra	ain diode				
I _S	source current	T _{amb} = 25 °C	-	400	mA
ESD maxir	num rating				
V _{ESD}	electrostatic discharge voltage	НВМ	<u>[3]</u>	2000	V

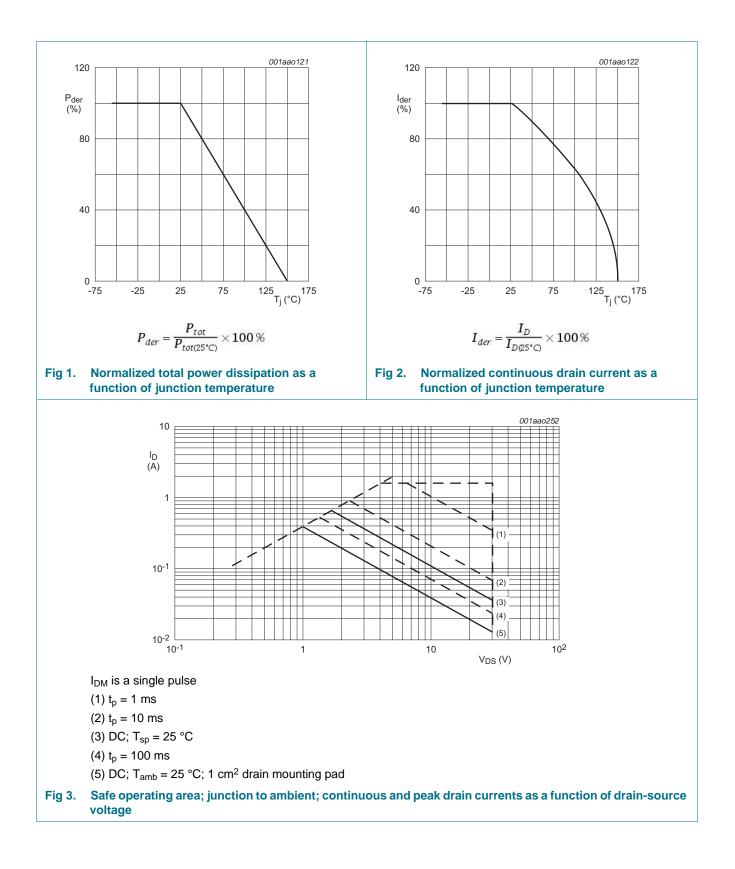
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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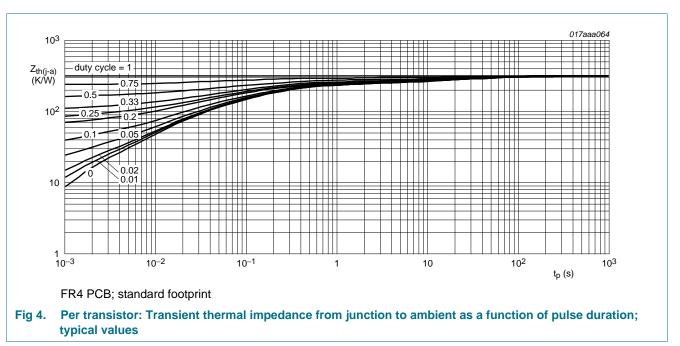
6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transist	or					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	330	380	K/W
			[2] _	280	320	K/W
R _{th(j-sp)}	thermal resistance from junction to solder poin	ıt	-	-	115	K/W
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	250	K/W

Table 6. Thermal characteristics

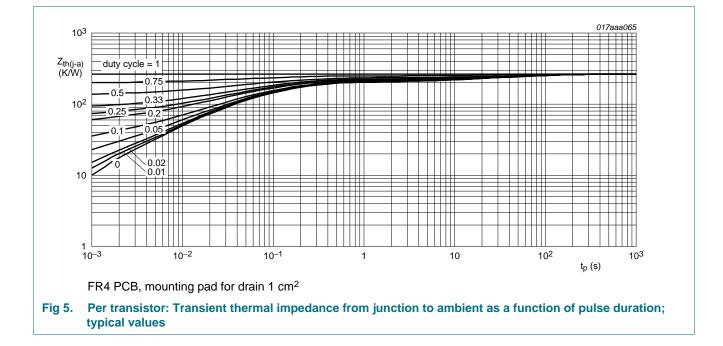
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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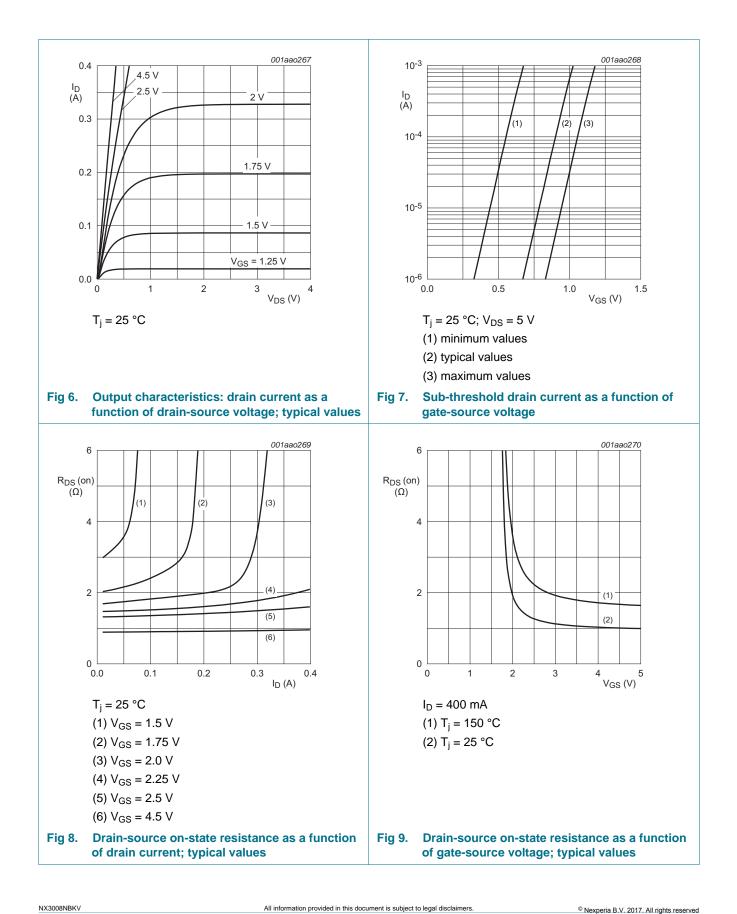


7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.6	0.9	1.1	V
DSS	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.2	1	μA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	0.2	1	μA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	10	-	nA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	10	-	nA
		$V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	1	-	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	1	-	nA
R _{DSon} drain-source on-st resistance	drain-source on-state	V _{GS} = 4.5 V; I _D = 350 mA; T _j = 25 °C	-	1	1.4	Ω
	resistance	V _{GS} = 4.5 V; I _D = 350 mA; T _j = 150 °C	-	1.8	2.5	Ω
		V _{GS} = 2.5 V; I _D = 200 mA; T _j = 25 °C	-	1.4	2.1	Ω
		V_{GS} = 1.8 V; I _D = 10 mA; T _j = 25 °C	-	2	2.8	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I _D = 350 mA; T _j = 25 °C	-	310	-	mS
Dynamic	characteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I _D = 400 mA; V _{GS} = 4.5 V;	-	0.52	0.68	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.17	-	nC
Q _{GD}	gate-drain charge		-	0.08	-	nC
C _{iss}	input capacitance	V_{DS} = 15 V; f = 1 MHz; V_{GS} = 0 V;	-	34	50	pF
C _{oss}	output capacitance	$T_j = 25 \ ^{\circ}C$	-	6.5	-	pF
C _{rss}	reverse transfer capacitance		-	2.2	-	pF
d(on)	turn-on delay time	V_{DS} = 20 V; R_L = 250 Ω ; V_{GS} = 4.5 V;	-	15	30	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
d(off)	turn-off delay time		-	69	138	ns
f	fall time		-	19	-	ns
Source-d	rain diode (per transistor)					
V _{SD}	source-drain voltage	I _S = 350 mA; V _{GS} = 0 V; T _j = 25 °C	0.47	0.85	1.2	V

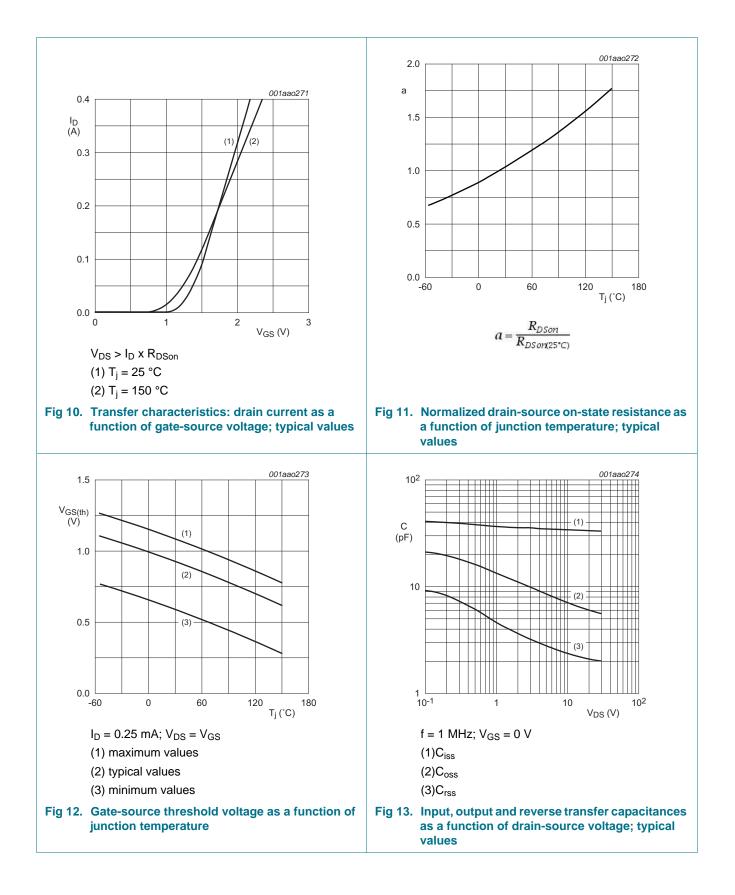
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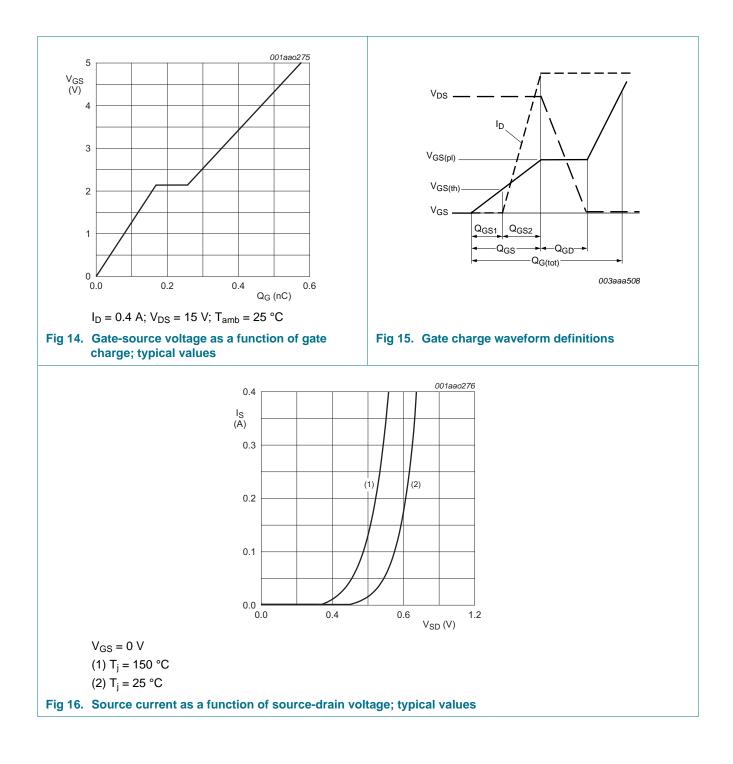
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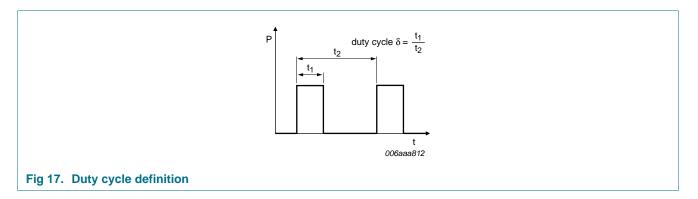
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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline

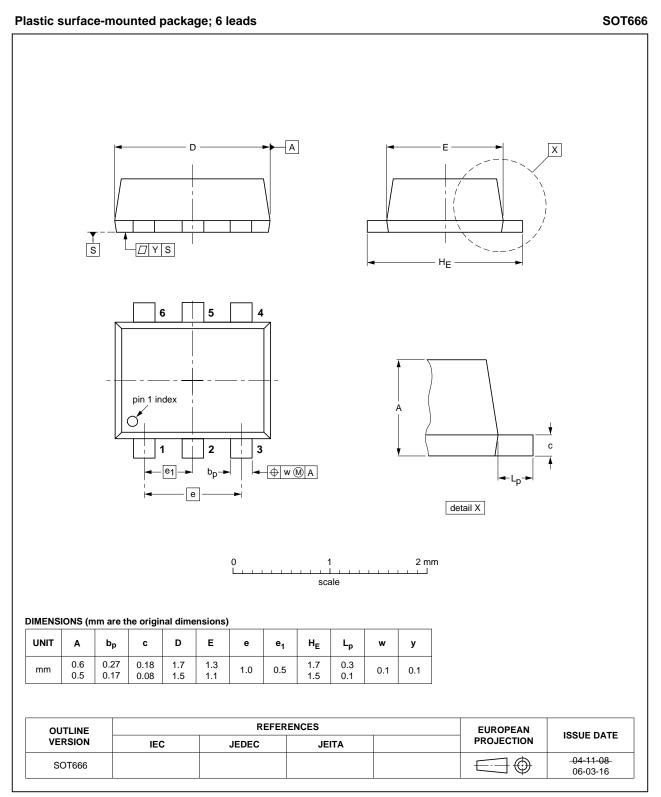
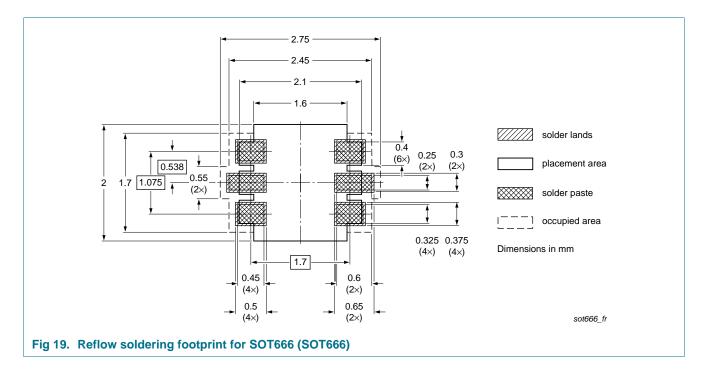


Fig 18. Package outline SOT666 (SOT666)

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10. Soldering



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11. Revision history

Table 8. Rev	Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
NX3008NBKV v	.1 20110801	Product data sheet	-	-		

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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